



DEVICE &
CIRCUIT DESIGN

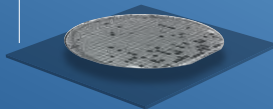
POWER
DEVICES



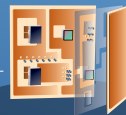
Fraunhofer
IISB

π -Fab[®]

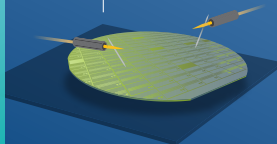
EPITAXY &
DEFECT ENGINEERING



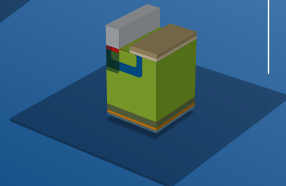
BEOL
PACKAGING



DEVICE
CHARACTERIZATION



SIMULATION
& MODELLING



Prototype Foundry π -Fab

150 mm SiC

π -Fab: Flexibility as a matter of principle

As part of Fraunhofer IISB's Division Semiconductor Technology, we operate our stand-alone brand π -Fab - a prototyping service that includes a continuous silicon carbide (SiC) and silicon (Si) CMOS process line in an industry-compatible and ISO 9001 certified environment.

π -Fab brings together four decades of experience in microelectronic research and development. During this time, we have expanded our activities to include industry-oriented, low-volume prototyping of customized electronic devices with a focus on power

devices, CMOS devices, passive devices, and sensors.

The unique feature of π -Fab is a high flexibility in wafer material and size. Our main objective is to support our customers with the fabrication of electron devices specific to their requirements. Our services further include particular processing steps or sequences. To keep flexibility high, an advanced contamination control is available. The process line is based on a 0.8 μm SiC and Si CMOS technology. Special attention is given to SiC device processing on 150 mm wafers.